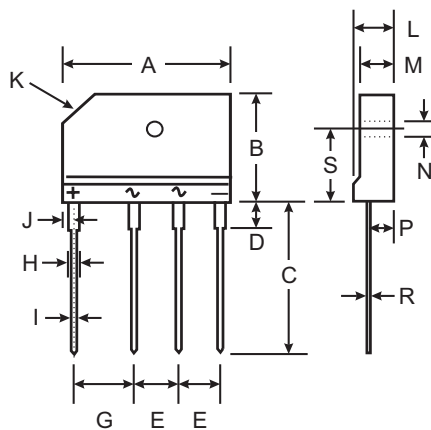


Features

- Glass Passivated Die Construction
- High Case Dielectric Strength of 1500V_{RMS}
- Low Reverse Leakage Current
- Surge Overload Rating to 350A Peak
- Ideal for Printed Circuit Board Applications
- UL Listed Under Recognized Component Index, File Number E94661
- **Lead Free Finish/RoHS Compliant (Note 4)**

Mechanical Data

- Case: GBJ
- Case Material: Molded Plastic. UL Flammability Classification 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Plated Leads, Solderable per MIL-STD-202, Method 208 (E3)
- Lead Free Plating (Tin Finish).
- Polarity: Molded on Body
- Mounting: Through Hole for #6 Screw
- Mounting Torque: 5.0 in-lbs Maximum
- Marking: Type Number
- Weight: 6.6 grams (approximate)



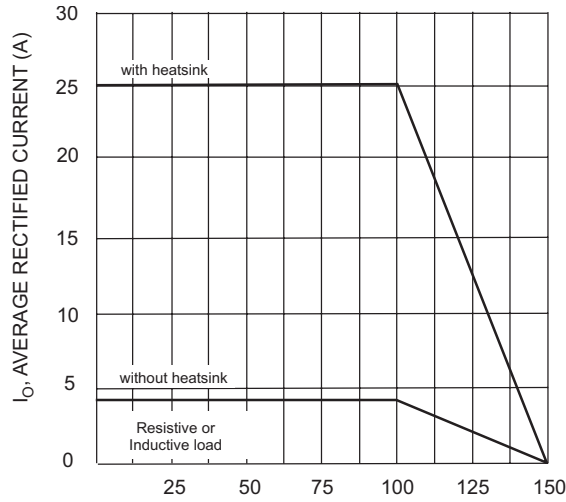
GBJ		
Dim	Min	Max
A	29.70	30.30
B	19.70	20.30
C	17.00	18.00
D	3.80	4.20
E	7.30	7.70
G	9.80	10.20
H	2.00	2.40
I	0.90	1.10
J	2.30	2.70
K	3.0 X 45°	
L	4.40	4.80
M	3.40	3.80
N	3.10	3.40
P	2.50	2.90
R	0.60	0.80
S	10.80	11.20
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

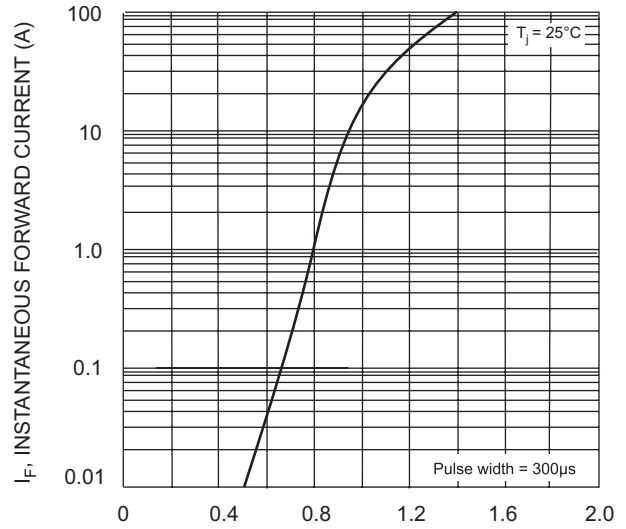
Single phase, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	GBJ 25005	GBJ 2501	GBJ 2502	GBJ 2504	GBJ 2506	GBJ 2508	GBJ 2510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Forward Rectified Output Current (Note 1) @ T _C = 100°C	I _O	25							A
Non-Repetitive Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	350							A
Forward Voltage (per element) @ I _F = 12.5A	V _{FM}	1.05							V
Peak Reverse Current @ T _C = 25°C at Rated DC Blocking Voltage @ T _C = 125°C	I _R	10 500							μA
I ² t Rating for Fusing (t < 8.3ms) (Note 1)	I ² t	510							A ² s
Typical Total Capacitance (per element) (Note 2)	C _T	85							pF
Typical Thermal Resistance Junction to Case (Note 3)	R _{θJC}	0.6							°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150							°C

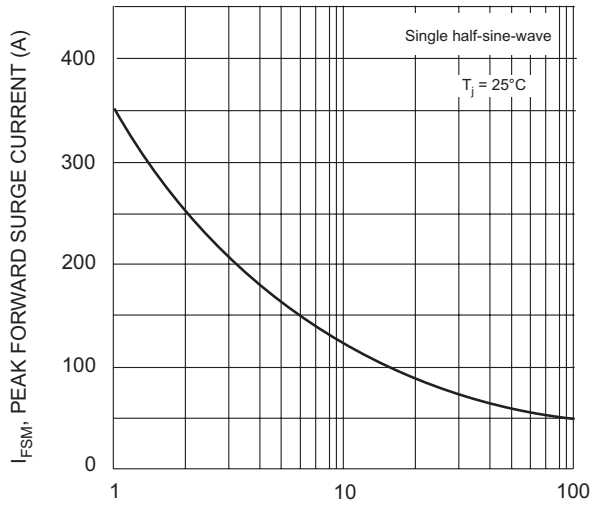
- Notes:
1. Non-repetitive, for t > 1ms and < 8.3 ms.
 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.
 3. Thermal resistance from junction to case per element. Unit mounted on 220 x 220 x 1.6mm aluminum plate heat sink.
 4. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.



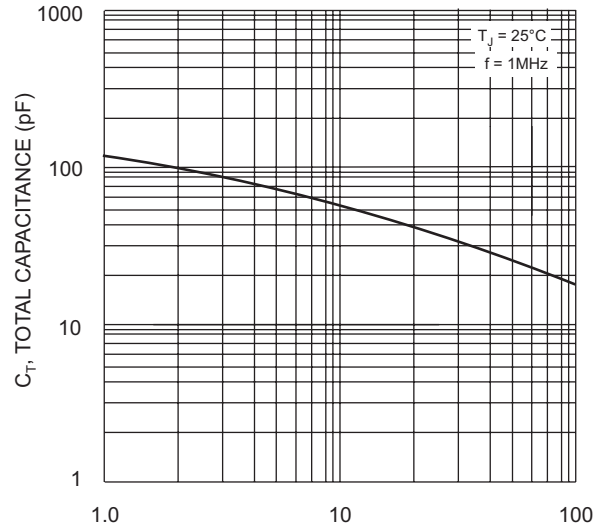
T_C , CASE TEMPERATURE ($^{\circ}\text{C}$)
Fig. 1 Forward Current Derating Curve



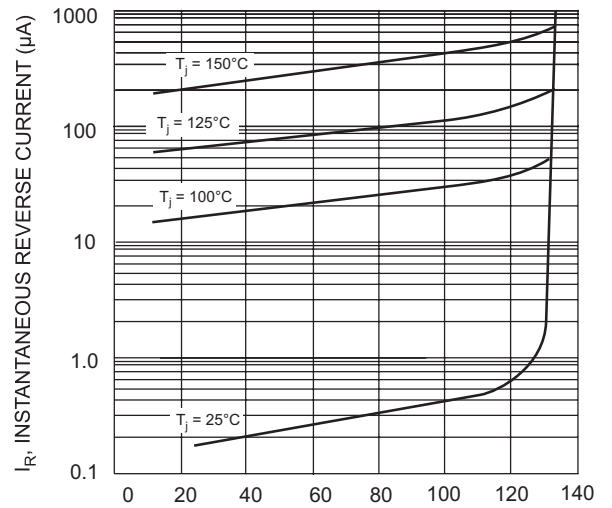
V_F , INSTANTANEOUS FORWARD VOLTAGE (V)
Fig. 2 Typical Forward Characteristics (per element)



NUMBER OF CYCLES AT 60 Hz
Fig. 3 Maximum Non-Repetitive Surge Current



V_R , REVERSE VOLTAGE (V)
Fig. 4 Typical Total Capacitance, Per Element



PERCENT OF RATED PEAK REVERSE VOLTAGE (%)
Fig. 5 Typical Reverse Characteristics

Ordering Information (Note 5)

Device	Packaging	Shipping
GBJ25005-F	GBJ	15/Tube
GBJ2501-F	GBJ	15/Tube
GBJ2502-F	GBJ	15/Tube
GBJ2504-F	GBJ	15/Tube
GBJ2506-F	GBJ	15/Tube
GBJ2508-F	GBJ	15/Tube
GBJ2510-F	GBJ	15/Tube

Notes: 5. For packaging details, visit our website at <http://www.diodes.com/datasheets/ap02008.pdf>.

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